

2N1595 - 2N1596 - 2N1597 - 2N1598 - 2N1599

SILICON THYRISTORS

Industrial-type, low-current silicon controlled rectifiers in a three-lead package ideal for printed-circuit applications Current handling capability of 1.6 amperes at junction temperetures to 100°C. Compliance to RoHS.

MAXIMUM RATINGS (*)

 $T_J=100$ °C unless otherwise noted

Symbol	Ratings	2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V _{RSM(REP)}	Peak reverse blocking voltage (*)	50	100	200	300	400	V
I _{T(RMS)}	Forward Current RMS (all conduction angles)	1.6		А			
I _{TSM}	Peak Surge Current (One Cycle, 60Hz, T _J =-20 to+100℃)	15		А			
Р _{бм}	Peak Gate Power – Forward	0.1		W			
P _{G(AV)}	Average Gate Power - Forward	0.01		W			
I _{GM}	Peak Gate Current – Forward	0.1		А			
V _{GFM}	Peak Gate Voltage - Forward 10			V			
V _{GRM}	Peak Gate Voltage - Reverse		10				V
TJ	Operating Junction Temperature Range -20 to +100		°C.				
T _{STG}	Storage Temperature Range	-20 to +120		Ŭ			



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ELECTRICAL CHARACTERISTICS

 $T_J{=}25^{\circ}{\rm C}$ unless otherwise noted, R $_{GK}{=}1000\Omega$

Symbol	Ratings		2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V _{DRM}	Peak Forward Blocking Voltage *	Min :	50	100	200	300	400	V
I _{RRM}	Peak Reverse Blocking Current (Rated V _{DRM} , T _J =100℃)		Max 1					mA
I _{DRM}	Peak Forward Blocking Current (Rated V_{DRM} with gate open, $T_J = 100$ °C)		Max 1					mA
I _{GT}	Gate Trigger Current Anode Voltage=7.0 Vdc, R_L =12 Ω		Typ : 2.0, Max : 10					mA
V _{GT}	Gate Trigger Voltage Anode Voltage=7.0 Vdc, R_L =12 Ω		Тур : 0.7, Мах : 3.0					V
	V _{DRM} = Rated, R _L =100Ω, T _J =100℃		Min : 0.2					
I _H	Holding Current Anode Voltage=7.0 Vdc, gate open			Тур : 5.0				
V _{TM}	Forward On Voltage I _T =1 Adc		Typ : 1.1, Max : 2.0					V
t _{gt}	Turn-On Time (t_d+t_r) I _{GT} =10 mA, I _T =1 A		Тур : 0.8					μS
tq	Turn-Off Time I _T =1 A, I _R =1 A, dv/dt=20 V/ μ s, T _J =100°C V _{DRM} = Rated Voltage		Тур : 10				μS	

(*) V_{DRM} or V_{RSM} can be applied for all types on a continuous dc basis without incurring damage.



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MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)			
	min	max	
А	8.50	9.39	
В	7.74	8.50	
С	6.09	6.60	
D	0.40	0.53	
E	-	0.88	
F	2.41	2.66	
G	4.82	5.33	
Н	0.71	0.86	
J	0.73	1.02	
К	12.70	-	
L	42°	48°	

Pin 1 :	kathode
Pin 2 :	Gate
Pin 3 :	Anode
Case :	anode



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